Unit: mm

TOSHIBA Insulated Gate Bipolar Transistor Silicon N Channel IGBT

# GT60N321

# High-Power Switching Applications Fourth Generation IGBT

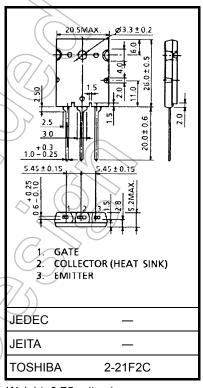
- FRD included between emitter and collector
- Enhancement mode type
- High speed IGBT :  $t_f = 0.25 \mu s$  (typ.) (I<sub>C</sub> = 60 A)

FRD :  $t_{rr} = 0.8 \mu s$  (typ.) (di/dt = -20 A/ $\mu s$ )

• Low saturation voltage:  $V_{CE (sat)} = 2.3 \text{ V (typ.)} (I_C = 60 \text{ A})$ 

# Absolute Maximum Ratings (Ta = 25°C)

Collector-Emitter Voltage         VCES         1000         V           Gate-Emitter Voltage         VGES         ±25         V           Collector Current         DC         IC         60         A           Emitter-Collector Forward Current         DC         IECF         15         A           I ms         IECFP         120         A						
Gate-Emitter Voltage	Characteristics		symbol	Rating	Unit	
DC	Collector-Emitter Voltage		V <sub>CES</sub>	1000	V	
Collector Current         1 ms         I <sub>CP</sub> 120           Emitter-Collector Forward Current         DC         I <sub>ECF</sub> 15           1 ms         I <sub>ECFP</sub> 120	Gate-Emitter Voltage		V <sub>GES</sub>	±25	À	
1 ms	Collector Current	DC	IC	60	A	
Forward Current 1 ms I <sub>ECFP</sub> 120	Collector Current	1 ms	I <sub>CP</sub>	120		
1 ms I <sub>ECFP</sub> 120	Emitter-Collector DC		I <sub>ECF</sub>	15	A	
Collector Dower Dissipation	Forward Current	1 ms	I <sub>ECFP</sub>	120		
(Tc = 25°C)	Collector Power Dissipation (Tc = 25°C)		Pc	170	W	
Junction Temperature T <sub>j</sub> 150 °C	Junction Temperature		T <sub>j</sub> ,	150	°C	
Storage Temperature T <sub>stg</sub> -55 to 150 °C	Storage Temperature		(T <sub>stg</sub>	-55 to 150	∕/°C	
Screw Torque 0.8 N·m	Screw Torque			0.8	И·ш	



Weight: 9.75 g (typ.)

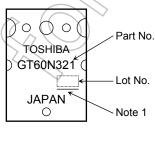
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

## **Equivalent Circuit**

# Collector Gate O Emitter

## Marking



Part No. (or abbreviation code)

Note 1

line under a Lot No. identifies the indication of product Labels. Not underlined: [[Pb]]/INCLUDES > MCV

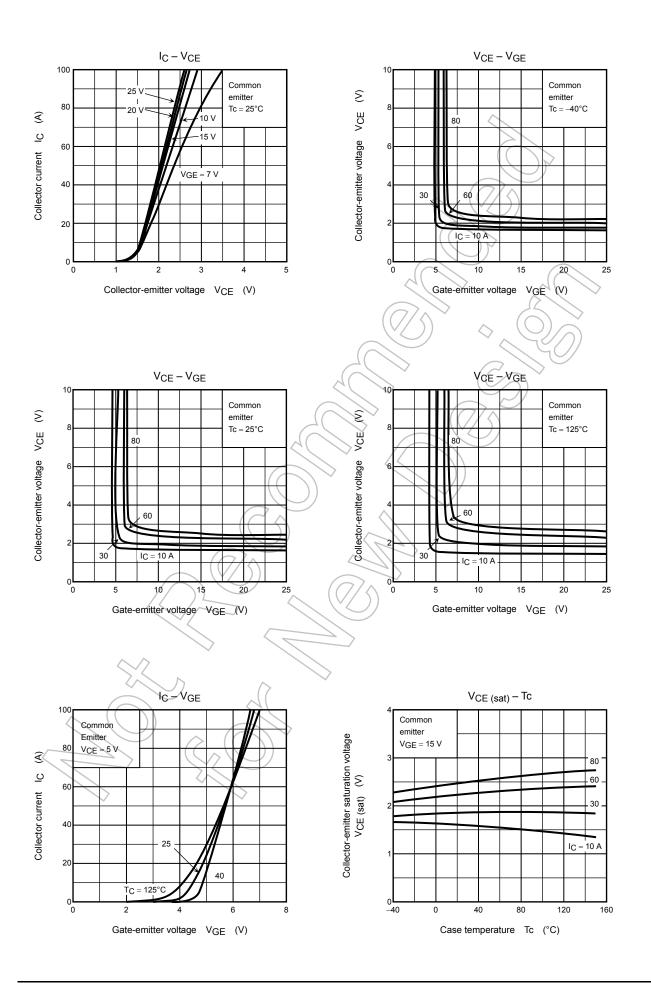
Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

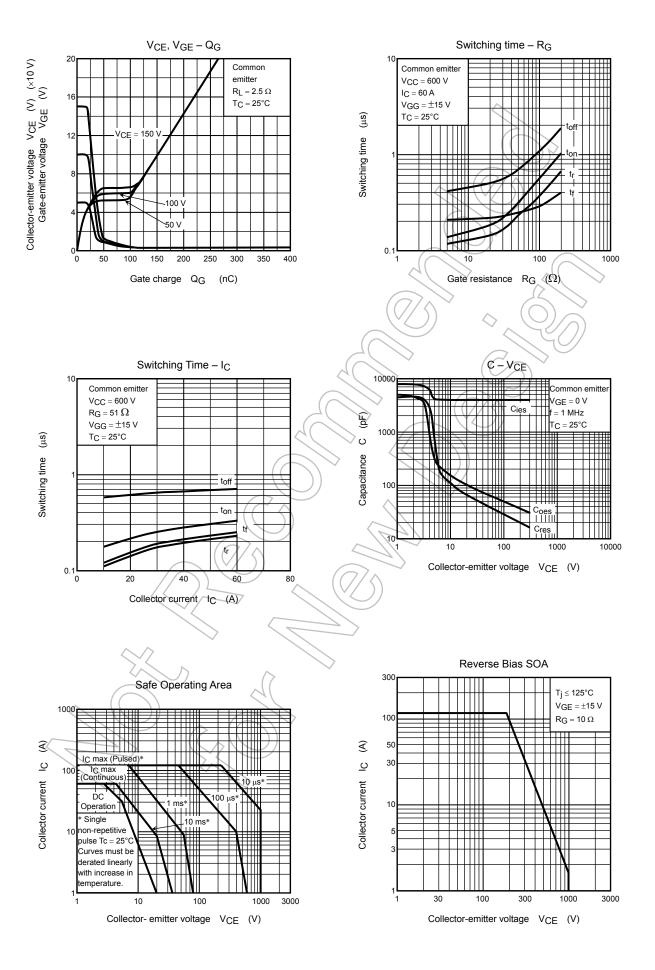
Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

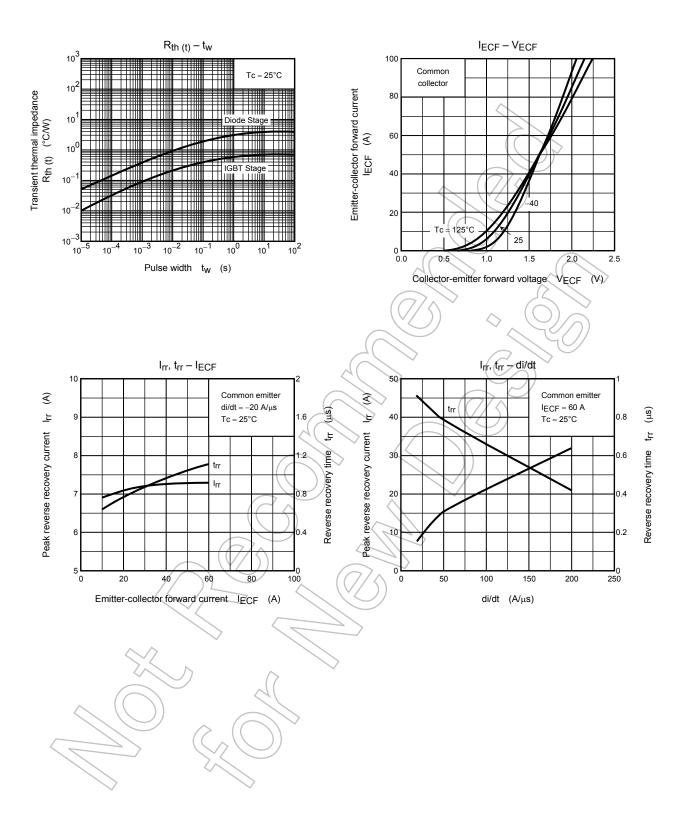
Start of commercial production 2000-03

# **Electrical Characteristics (Ta = 25°C)**

Chara	acteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate Leakage Cu	rrent	I <sub>GES</sub>	$V_{GE} = \pm 25 \text{ V}, V_{CE} = 0$	_	_	±500	nA
Collector Cut-off (	Current	I <sub>CES</sub>	V <sub>CE</sub> = 1000 V, V <sub>GE</sub> = 0	_	_	1.0	mA
Gate-Emitter Cut-	off Voltage	V <sub>GE</sub> (OFF)	$I_C = 60 \text{ mA}, V_{CE} = 5 \text{ V}$	3.0	_	6.0	V
Collector-Emitter	Saturation Voltage	V <sub>CE</sub> (sat) (1)	I <sub>C</sub> = 10 A, V <sub>GE</sub> = 15 V		1.6	2.3	V
Collector-Emitter	Saturation Voltage	V <sub>CE (sat)</sub> (2)	I <sub>C</sub> = 60 A, V <sub>GE</sub> = 15 V	1	2.3	2.8	V
Input Capacitance	9	C <sub>ies</sub>	V <sub>CE</sub> = 10 V, V <sub>GE</sub> = 0, f = 1 MHz	7/~	4000	_	pF
	Rise Time	t <sub>r</sub>	51 Ω C OI	$\bigcirc)$	0.23	_	
Switching Time Fall Time	Turn-on Time	t <sub>on</sub>		<u> </u>	0.33	_	μS
	Fall Time	t <sub>f</sub>		_	0.25	0.40	
	Turn-off Time	t <sub>off</sub>	15 V 600 V	- (	0.70		
Emitter-Collector	Forward Voltage	V <sub>ECF</sub>	I <sub>EC</sub> = 15 A, V <sub>GE</sub> = 0		1.2	1.9	V
Reverse Recover	y Time	t <sub>rr</sub>	$I_F = 15 \text{ A}, V_{GE} = 0, di/dt = -20 \text{ A}/\mu\text{s}$	1	0.8	2.5	μS
Thermal Resistan	ce (IGBT)	R <sub>th(j-c)</sub>			~_	0.74	°C/W
Thermal Resistan	ce (Diode)	R <sub>th(j-c)</sub>				4.0	°C/W







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